NTS260ESF, NRVTS260ESF

Very Low Forward Voltage Trench-based Schottky Rectifier

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 11.7 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds
- MSL 1

Typical Applications

- Switching Power Supplies including Compact Adapters and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation



ON Semiconductor®

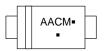
www.onsemi.com

TRENCH SCHOTTKY RECTIFIER 2.0 AMPERES 60 VOLTS



SOD-123FL CASE 498

MARKING DIAGRAM



AAC = Specific Device Code

M = Date Code■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NTS260ESFT3G	SOD-123FL (Pb-Free)	10,000/ Tape & Reel
NRVTS260ESFT3G	SOD-123FL (Pb-Free)	10,000/ Tape & Reel
NTS260ESFT1G	SOD-123FL (Pb-Free)	3,000/ Tape & Reel
NRVTS260ESFT1G	SOD-123FL (Pb-Free)	3,000/ Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTS260ESF, NRVTS260ESF

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	60	V
Average Rectified Forward Current (T _L = 128°C)	Io	2.0	Α
Peak Repetitive Forward Current (Square Wave, 20 kHz, T _L = 137°C)	I _{FRM}	4.0	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	50	Α
Storage and Operating Junction Temperature Range (Note 1)	T _{stg} , T _J	-65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Note 2)	$\Psi_{\sf JCL}$	24.4	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	85	°C/W
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{ heta JA}$	330	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
$\label{eq:maximum Instantaneous Forward Voltage (Note 4)} \begin{tabular}{l} (I_F = 1.0 \ A, \ T_J = 25^\circ C) \\ (I_F = 2.0 \ A, \ T_J = 25^\circ C) \\ (I_F = 1.0 \ A, \ T_J = 125^\circ C) \\ (I_F = 2.0 \ A, \ T_J = 125^\circ C) \\ \end{tabular}$	V _F	0.55 0.65 0.47 0.58	V
Maximum Instantaneous Reverse Current (Note 4) (Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 125^{\circ}C$)	I _R	12 3	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

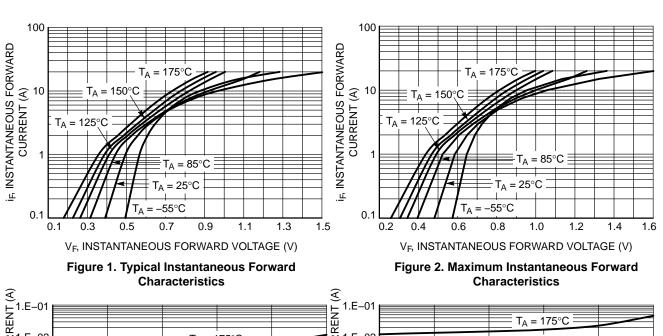
2. Mounted with 700 mm² copper pad size (Approximately 1 in²) 1 oz FR4 Board.

- 3. Mounted with pad size approximately 20 mm² copper, 1 oz FR4 Board. 4. Pulse Test: Pulse Width \leq 380 μ s, Duty Cycle \leq 2.0%.

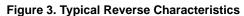
^{1.} The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

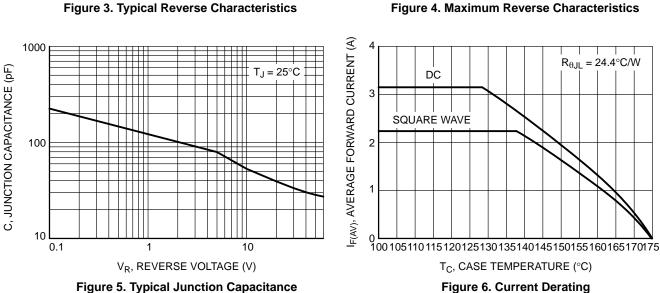
NTS260ESF, NRVTS260ESF

TYPICAL CHARACTERISTICS



 $\begin{array}{c} \text{(A)} & \text{INSTANTANEOUS REVERSE CURRENT} \\ \text{(A)} & \text{INSTANTANEOUS REVERSE CURRENT} \\ \text{(B)} & \text{(B)} & \text{(B)} \\ \text{(C)} & \text{(B)} & \text{(C)} \\ \text{(C)} & \text{(C)} & \text{(C)} & \text{(C)} \\ \text{(C)} & \text{(C)} \\ \text{(C)} & \text{(C)} & \text{(C)} \\ \text{(C)} & \text{(C)} & \text{(C)} \\ \text{(C)}$ $T_A = 175^{\circ}C$ $T_A = 150^{\circ}C$ $T_A = 150$ °C $T_A = 125^{\circ}C$ T_A = 125°C $T_A = 85^{\circ}C$ IR, INSTANTANEOUS $T_A = 85^{\circ}C$ 1.E-05 T_A = 25°C 1.E-06 $T_A = 25^{\circ}C$.E-07 40 60 20 30 50 10 20 30 40 50 60 10 V_R, INSTANTANEOUS REVERSE VOLTAGE (V) V_R, INSTANTANEOUS REVERSE VOLTAGE (V)

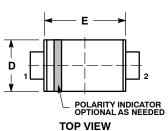


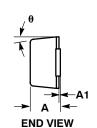


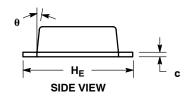


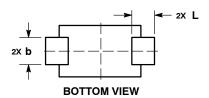
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DATE 10 MAY 2013

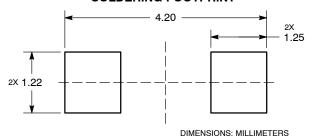








RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- ES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH.
 DIMENSIONS D AND J ARE TO BE MEASURED ON FLAT SECTION
 OF THE LEAD: BETWEEN 0.10 AND 0.25 MM FROM THE LEAD TIP.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	0.95	0.98	0.035	0.037	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.70	0.90	1.10	0.028	0.035	0.043
С	0.10	0.15	0.20	0.004	0.006	0.008
D	1.50	1.65	1.80	0.059	0.065	0.071
E	2.50	2.70	2.90	0.098	0.106	0.114
L	0.55	0.75	0.95	0.022	0.030	0.037
HE	3.40	3.60	3.80	0.134	0.142	0.150
θ	0°	-	8°	0°	-	8°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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